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Nov 2009 Power-SPMTM

FP7G150US60

Transfer Molded Type IGBT Module

General Description

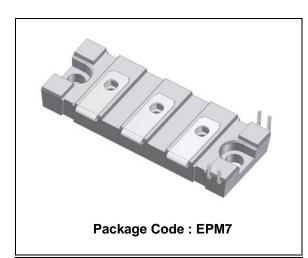
Fairchild's New IGBT Modules (Transfer Molded Type) provide low conduction and switching losses as well as short circuit ruggedness. They are designed for applications such as Motor control, Uninterrupted Power Supplies (UPS) and general Inverters where short circuit ruggedness is a required feature.

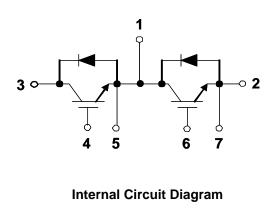
Features

- Short Circuit rated 10us @Tc=100°C, Vge=15V
- · High Speed Switching
- Low Saturation Voltage : Vce(sat) =2.3V @Ic=150A
- · High Input Impedance
- Fast & Soft Anti-Parallel FWD

Application

- Welders
- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls
- UPS

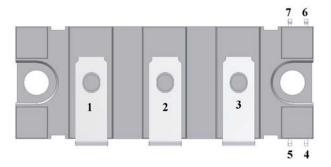




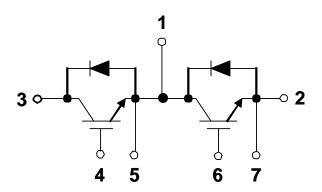
Absolute Maximum Ratings

Symbol	Description		Rating	Units
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
I _C	Collector Current	@ T _C = 25°C	150	A
I _{CM (1)}	Maximum Pulsed Collector Current		300	A
IF	Diode Continuous Forward Current	@ T _C = 100°C	150	Α
I _{FM}	Diode Maximum Forward Current		300	А
T _{SC}	Short Circuit Withstand Time	@ T _C = 100°C	10	us
P _D	Maximum Power Dissipation	@ T _C = 25°C	450	W
T _J	Operating Junction Temperature		-40 to +125	°C
T _{stg}	Storage Temperature Range		-40 to +125	°C
V _{iso}	Isolation Voltage	@ AC 1minute	2500	V
Mounting	Power Terminals Screw : M5		2.0	N.m
Torque	Mounting Screw : M5		2.0	N.m

Pin Configuration and Pin Description



Top View



Internal Circuit Diagram

Pin Description

Pin Number	Pin Description
1	Emitter of Q1, IGBT, Collector of Q2, IGBT
2	Emitter of Q2, IGBT
3	Collector of Q1, IGBT
4	Gate of Q1, IGBT
5	Emitter of Q1, IGBT
6	Gate of Q2, IGBT
7	Emitter of Q2, IGBT

Electrical Characteristics ($T_J = 25$ °C, Unless Otherwise Specified)

	Parameter	Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250\mu A$	600	-	-	V
ΔBV _{CES} / ΔΤ _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	-	0.6	-	٧
I _{CES}	Collector Cut-off Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	250	uA
I _{GES}	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	± 100	nA
On Char	acteristics					
V _{GE(th)}	G-E Threshold Voltage	V _{GE} = 0V, I _C =150mA	5.0	6.0	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 150A, V _{GE} = 15V	-	2.3	2.8	V
Dynamic	: Characteristics					
C _{ies}	Input Capacitance			11.2		nF
C _{oes}	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$		1.03		nF
C _{res}	Reverse Capacitance	f = 1MHz		0.1		nF
	g Characteristics	1		1		
t _{d(on)}	Turn-On Delay Time		-	45	-	ns
t _r	Rise Time	-	-	35	-	ns ns
t _r	Rise Time Turn-Off Delay Time	- - - - V _{CC} = 300 V, I _C = 150A,	-	35 135		
t _r t _{d(Off)}	Rise Time	$R_G = 2.4\Omega, V_{GE} = 15V$		35	-	ns
t _r t _{d(off)} t _f	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss			35 135	-	ns ns
t _r t _{d(off)} t _f E _{on}	Rise Time Turn-Off Delay Time Fall Time	$R_G = 2.4\Omega, V_{GE} = 15V$	-	35 135 70	-	ns ns ns mJ
t _r t _{d(off)} t _{d(off)} E _{on} E _{off}	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$R_G = 2.4\Omega, V_{GE} = 15V$	-	35 135 70 0.66	-	ns ns ns mJ
t _r t _{d(off)} t _f E _{on} E _{off} E _{ts}	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_G = 2.4\Omega, V_{GE} = 15V$	-	35 135 70 0.66 2.7	-	ns ns ns mJ
tr td(off) tf Eon Eoff Ets	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss	$R_G = 2.4\Omega, V_{GE} = 15V$		35 135 70 0.66 2.7 3.36		ns ns ns mJ mJ
t _r	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time	$R_G = 2.4\Omega$, $V_{GE} = 15V$ Inductive Load, $T_C = 25^{\circ}C$		35 135 70 0.66 2.7 3.36 45	-	ns ns ns mJ mJ
tr td(off) tf Eon Eoff Ets td(on) tr	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	$R_{G}=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=150A,$ $R_{G}=2.4\Omega,\ V_{GE}=15V$		35 135 70 0.66 2.7 3.36 45 35	-	ns ns ns mJ mJ mJ ns
t _r t _{d(off)} t _f E _{on} E _{off} E _{ts}	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time	$R_G = 2.4\Omega$, $V_{GE} = 15V$ Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V}$, $I_C = 150\text{A}$,		35 135 70 0.66 2.7 3.36 45 35	-	ns ns ns mJ mJ ns ns
tr td(off) tf Eon Eoff Ets td(on) tr	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	$R_{G}=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=150A,$ $R_{G}=2.4\Omega,\ V_{GE}=15V$		35 135 70 0.66 2.7 3.36 45 35 160	-	ns ns ns mJ mJ ms ns ns ns
tr td(off) tf Eon Eoff Ets td(on) tr td(off)	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	$R_{G}=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=150A,$ $R_{G}=2.4\Omega,\ V_{GE}=15V$		35 135 70 0.66 2.7 3.36 45 35 160 170		ns ns ns mJ mJ ns ns ns mJ mJ ns ns ns ns ns ns
tr td(off) tf Eon Eoff tts td(on) tr td(off)	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_{G}=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_{C}=25^{\circ}C$ $V_{CC}=300\ V,\ I_{C}=150A,$ $R_{G}=2.4\Omega,\ V_{GE}=15V$		35 135 70 0.66 2.7 3.36 45 35 160 170 1.5		ns ns ns ns mJ mJ ns ns ns
tr td(off) td(off) te ton toff td(on) tt td(on) tr td(off) tf te ton tc tf td(off) tf	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Total Switching Loss	$R_G=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_C=25^\circ C$ $V_{CC}=300\ V,\ I_C=150A,$ $R_G=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_C=125^\circ C$		35 135 70 0.66 2.7 3.36 45 35 160 170 1.5		ns ns ns mJ mJ ns ns ns ms mJ ms ns ns ns ns ns mJ mJ mJ
tr td(off) tf Eon Eoff Ets td(on) tr td(off) tr Eon Etd(off) tf Eon Eoff Eon	Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Turn-Off Switching Loss Total Switching Loss Short Circuit Withstand Time	$R_G=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_C=25^\circ C$ $V_{CC}=300\ V,\ I_C=150A,$ $R_G=2.4\Omega,\ V_{GE}=15V$ Inductive Load, $T_C=125^\circ C$	- - - - - - - - - - - 10	35 135 70 0.66 2.7 3.36 45 35 160 170 1.5 4.4 5.9		ns ns ns mJ mJ ns us

Electrical Characteristics of DIODE ($T_J = 25$ °C, Unless Otherwise Specified)

Symbol	Parameter	Con	ditions	Min	Тур	Max	Units
V _{FM}	Diada Famurad Valtaria	1 4504	T _C = 25°C	-	1.8	2.8	\ /
Diode Forward Voltage	I _F = 150A	T _C = 100°C	-	1.7	-	V	
	D: 1 D D T		T _C = 25°C	-	115	165	
t _{rr}	Diode Reverse Recovery Time		T _C = 100°C	-	190	-	ns
		I _F = 150A	T _C = 25°C	-	23	33	
ırr	Diode Peak Reverse Recovery Current	di / dt = 300 A/us	T _C = 100°C	-	45	-	Α
Q _{rr} Diode Reverse Recovery Charge		T _C = 25°C	-	1322	-		
		T _C = 100°C	-	4307	-	nC	

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)	-	0.22	°C/W
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)	-	0.54	°C/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05	-	°C/W
Weight	Weight of Module	-	90	g

Typical Performance Characteristics

Fig 1. Typical Output Characteristics

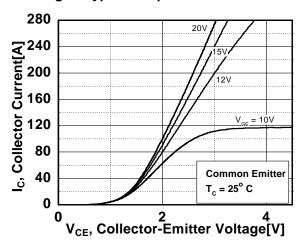


Fig 2. Typical Saturation Voltage Characteristics

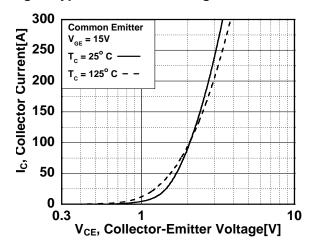


Fig 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

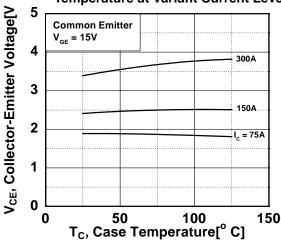


Fig 4. Load Current vs. Frequency

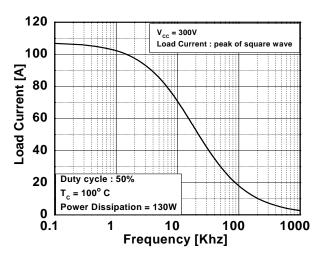


Fig 5. Saturation Voltage vs. V_{GE}

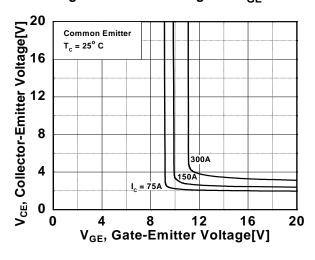
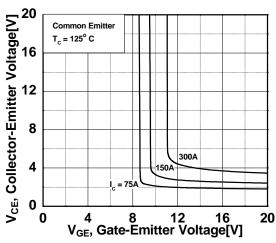


Fig 6. Saturation Voltage vs. V_{GE}



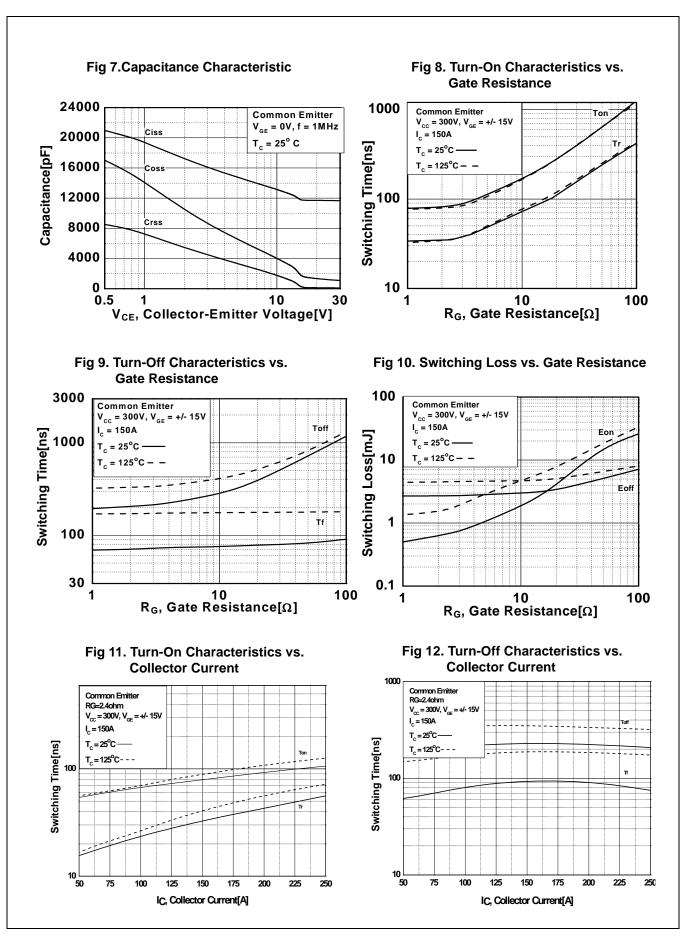


Fig 13. Switching Loss vs. Collector

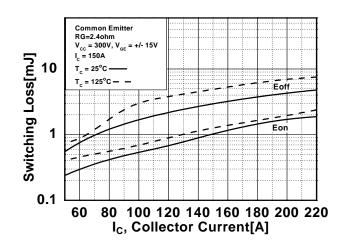


Fig 14. Gate Charge Characteristics

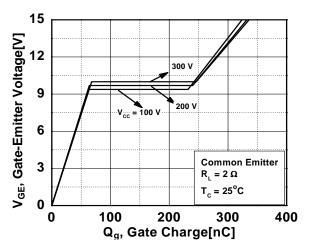


Fig 15. FBSOA Characteristics

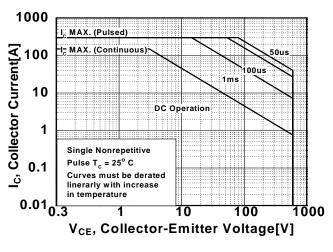


Fig 16. Turn-Off SOA Characteristics

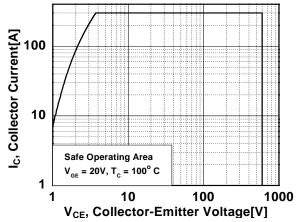


Fig 17. RBSOA Characteristics

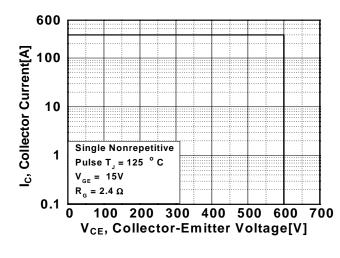


Fig 18. Transient Thermal Impedance

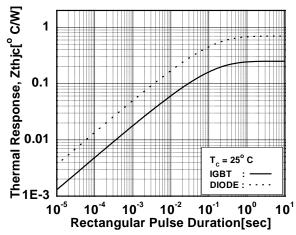


Fig 19. Forward Characteristics

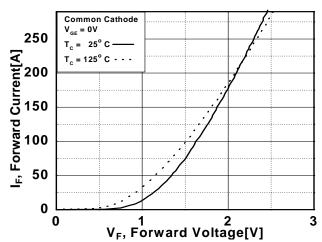
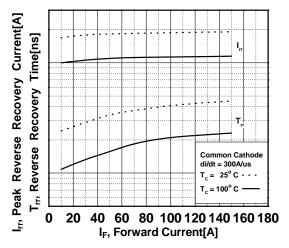
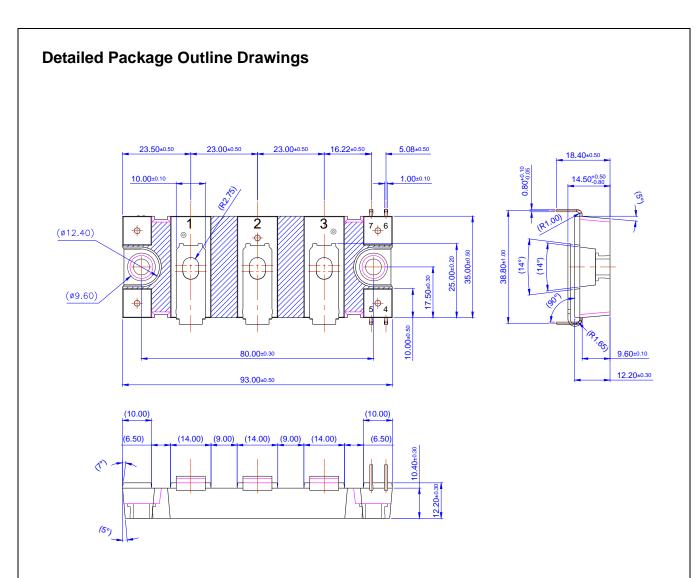


Fig 20. Reverse Recovery Characteristics





	FP7G150US60 Transfer Molded Type IGBT Module





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